adjacent the gate sidewall spacers, which conductive layer adjacent the gate sidewall spacers serves as a source/drain region.--

IN THE CLAIMS

Please substitute the following clean copy text for the pending claims of the same number:

15. (Amended) A thin film transistor structure, comprising:

an insulating substrate;

a polysilicon layer over the substrate;

a gate structure over the polysilicon layer, wherein the gate structure includes a gate layer, a gate dielectric layer between the gate layer and the polysilicon layer and a spacer on each side of the gate layer; and

a conductive layer over the gate layer and the polysilicon layer adjacent to the spacers, wherein the conductive layer adjacent to the spacers serves as a source/drain region.

17. (Amended) The structure of claim 15, wherein the conductive layer comprises an in-situ doped silicon-germanium (SiGe) layer.

18. (Amended) The structure of claim 15, wherein the conductive layer comprises a tungsten layer.

19. (Amended) The structure of claim 15, wherein the conductive layer comprises a metal silicide layer.

20. (Amended) The structure of claim 15, wherein the spacer comprises a tetra-ethyl-ortho-silicate (TEOS) layer.